GaAlAs Infrared Emitting Diode



ODE-208-1000A (Z)

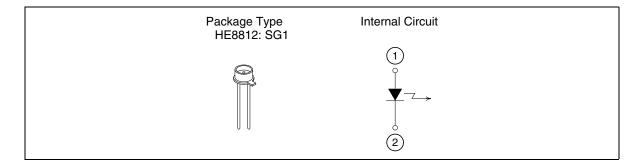
Rev.1 Jan. 2003

Description

The HE8812SG is a GaAlAs double heterojunction structure 870 nm band light emitting diode. It is suitable for use as the light source in a wide range of optical control and sensing equipment.

Features

• High efficiency and high output power





Absolute Maximum Ratings

$$(T_c = 25^{\circ}C)$$

| Item | Symbol | Value | Unit |
|-----------------------|----------------|------------|------|
| Forward current | I _F | 250 | mA |
| Reverse voltage | V _R | 3 | V |
| Operating temperature | Topr | -20 to +60 | °C |
| Storage temperature | Tstg | -40 to +90 | °C |

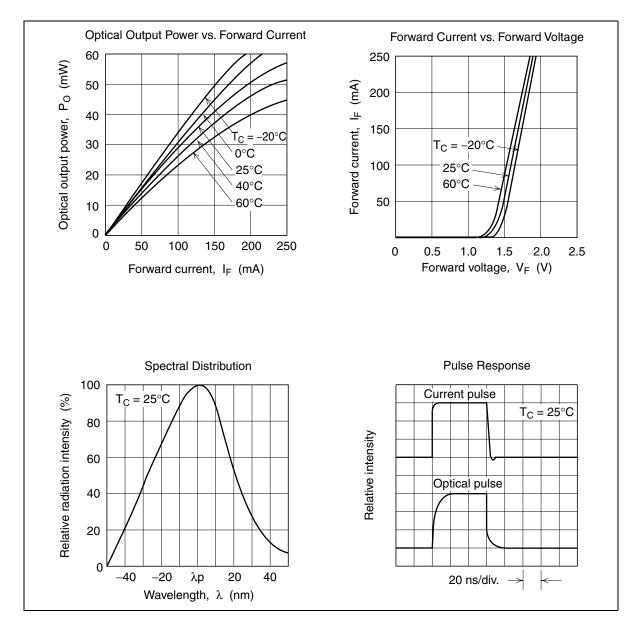
Optical and Electrical Characteristics

$$(T_c = 25^{\circ}C)$$

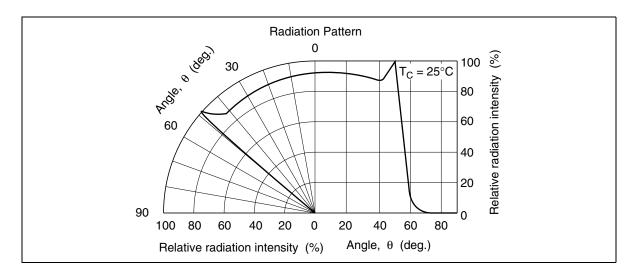
| Item | Symbol | Min | Тур | Max | Unit | Test Conditions |
|----------------------|----------------|-----|-----|-----|------|---------------------------------|
| Optical output power | Po | 40 | _ | _ | mW | I _F = 200 mA |
| Peak wavelength | λр | 840 | 870 | 900 | nm | I _F = 200 mA |
| Spectral width | Δλ | _ | 50 | 60 | nm | I _F = 200 mA |
| Forward voltage | V _F | _ | _ | 2.5 | V | I _F = 200 mA |
| Reverse current | I _R | _ | _ | 100 | μΑ | V _R = 3 V |
| Capacitance | Ct | _ | 30 | _ | pF | V _R = 0 V, f = 1 MHz |
| Rise time | t _r | _ | 10 | _ | ns | I _F = 50 mA |
| Fall time | t _f | _ | 10 | _ | ns | I _F = 50 mA |



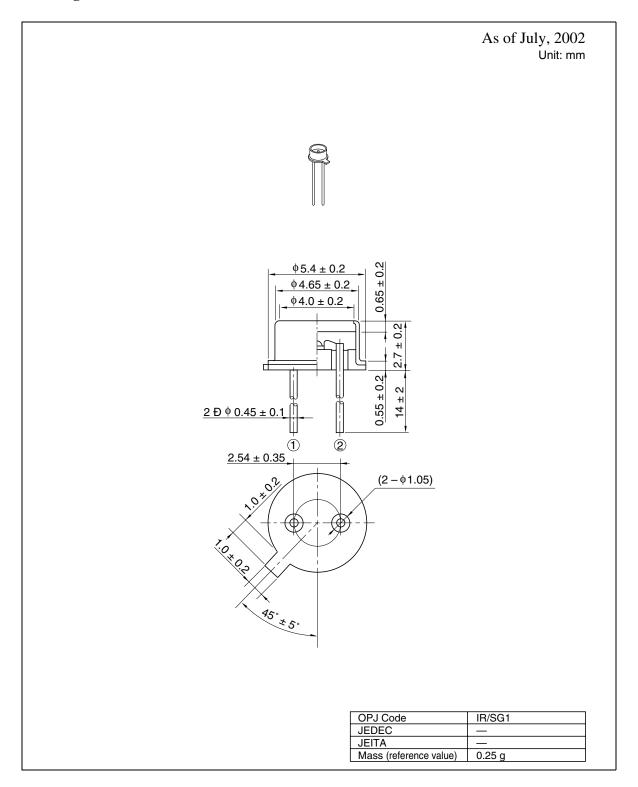
Typical Characteristic Curves



Typical Characteristic Curves (cont)



Package Dimensions





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- 2. This product contains gallium arsenide (GaAs), which may seriously endanger your health even at very low doses. Please avoid treatment which may create GaAs powder or gas, such as disassembly or performing chemical experiments, when you handle the product.

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Sales Offices



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